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& TRAUE ME			U.S. PATENT DOCUMENTS				-			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING (IF APPR	DATE OPRIATE)			
MS	US 2001/0000866 A1	5/10/01	Sneh et al.	_						
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VP E	FORM P10-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  DISCLOSURE STATEMENT	ATTY. DOCKET NO. SEPP11.001AUS	APPLICATION NO. 09/836,674
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MS	1	6,015,590	1/18/00	Suntola et al.				
MS	2	5,855,680	1/5/99	Soininen et al.		_	_	
MS	3	4,389,973	6/28/93	Suntola et al.		~	_	
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INITIAL						YES	NO	
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	5	Handbook of Grystal Growth 3, Thin Films and epitaxy, Part B. Growth Mechanisms and Dyannics, Page 625.					
MI	6	Niinisto et al., "ALD precursor chemistry: evolution and future challenges," Journal de Physsique IV. Vol. 9 (1999), pages Pr8-837-Pr8-852.					
MS	7	M. Leskela et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," Materials Science & Engineering, Vol. B41 (1996), pages 23-29.					
19	8	Tuomo Suntola, "Atomic layer epitaxy," Thin Solid Films, Vol 216 (1992), pages 84-89					
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\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.